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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete If Known		
			Application Number	NEW 10/758,008	
			Filing Date	January 7, 2004	
			First Named Inventor	Jiutao Li	
			Art Unit	NTA 2815	
			Examiner Name	Not Yet Assigned Fenty	
Sheet	1	of	9	Attorney Docket Number	M4065.0609/P609/P609-C

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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Examiner Signature	<i>James L. Fenty</i>	Date Considered	8/3/15
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*EXAMINER: Initial reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

† Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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Examiner Signature	<i>John L. Fenty</i>	Date Considered	8/3/5
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